

NVBG015N065SC1

Silicon Carbide MOSFET, N-Channel, 650V, 12 mΩ, D2PAK-7L

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

- Qualified for Automotive According to AEC-Q101
- 650V rated
- Max RDS(on) = 18 mΩ at Vgs = 18V, Id = 75A
- High Speed Switching and Low Capacitance
- 100% UIL Tested
- Devices are RoHS Compliant
- Automotive Grade
- Automotive DC/DC
- Automotive PFC
- Automotive On Board Charger
- Automotive DC/DC converter for EV/PHEV

	Pricing (\$/Unit)	Compliance	Status	Family	Blocking Voltage BV _{DSS} (V)	I _{D(max)} (A)	R _{DS(on)} Typ @ 25°C (mΩ)	Q _g Total (nC)	Output Capacitance (pF)	T _j Max (°C)	Package Type
NVBG015N065SC1	18.5662		Active	M2	650	145	12	283	424	175	D2PAK7 (TO-263-7L HV)